



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

2SC2412 TRANSISTOR (NPN)

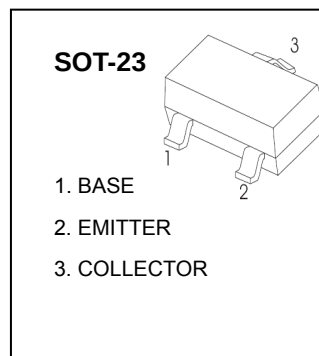
FEATURES

- Low C_{ob} , $C_{ob} = 2.0 \text{ pF (Typ)}$.

MARKING : BQ, BR, BS

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current -Continuous	150	mA
P_C	Collector Power Dissipation	200	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu\text{A}, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=6\text{V}, I_C=1\text{mA}$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.4	V
Transition frequency	f_T	$V_{CE}=12\text{V}, I_C=2\text{mA}, f=100\text{MHz}$		160		MHz
Collector output capacitance	C_{ob}	$V_{CB}=12\text{V}, I_E=0, f=1\text{MHz}$		2.0	3.5	pF

CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	120 - 270	180 - 390	270 - 560
Marking	BQ	BR	BS

Typical Characteristics

2SC2412

